

AMENDMENTS TO THE CLAIMS

1 - 4 (Cancelled).

5. (New) A production method for a laminated type semiconductor ceramic element comprising

providing a mixture comprising a barium compound, a titanium compound and a nickel compound,

calcining the mixture to obtain a calcined product;

forming a ceramic green sheet comprising the calcined product;

applying a conductive paste for forming an internal electrode layer of the laminated type semiconductor ceramic element on the ceramic green sheet;

laminating the ceramic green sheet so as to provide a laminated product; and

baking the laminated product under a reducing atmosphere so as to form a laminated semiconductor ceramic element.

6. (New) The production method of claim 5 wherein the mixture calcined contains a boron compound.

7. (New) The production method of claim 6 wherein the boron compound is about 0.2 to 20 mol%.

8. (New) The production method of claim 7 wherein the nickel compound is present in the mixture in a positive amount up to about 0.2 mol%.

9. (New) The production method of claim 8 wherein an external electrode electrically conducted to the internal electrode is formed on the laminated semiconductor ceramic element.

10. (New) The production method according to claim 9 in which the baked laminated product is reoxidized.

11. (New) The production method according to claim 10 wherein the laminated product is baked at a temperature of 900 to 1300°C for 0.5 to 5 hours.

12. (New) The production method according to claim 11 wherein the conductive paste contains nickel.

13. (New) The production method according to claim 12 comprising forming the mixture of the barium compound, titanium compound and nickel compound.

14. (New) The production method of claim 5 wherein the nickel compound is present in the mixture in a positive amount up to about 0.2 mol%.

15. (New) The production method of claim 14 wherein an external electrode electrically conducted to the internal electrode is formed on the laminated semiconductor ceramic element.

16. (New) The production method according to claim 15 in which the baked laminated product is reoxidized.

17. (New) The production method according to claim 16 wherein the laminated product is baked at a temperature of 900 to 1300°C for 0.5 to 5 hours.

18. (New) The production method according to claim 17 wherein the conductive paste contains nickel.

19. (New) The production method according to claim 18 comprising forming the mixture of the barium compound, titanium compound and nickel compound.

20. (New) The production method of claim 5 in which an external electrode electrically conducted to the internal electrode is formed on the laminated semiconductor ceramic element.

21. (New) The production method according to claim 5 in which the baked laminated product is reoxidized.

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22. (New) The production method according to claim 5 wherein the laminated product is baked at a temperature of 900 to 1300°C for 0.5 to 5 hours.

23. (New) The production method according to claim 5 wherein the conductive paste contains nickel.

24. (New) The production method according to claim 5 comprising forming the mixture of the barium compound, titanium compound and nickel compound.